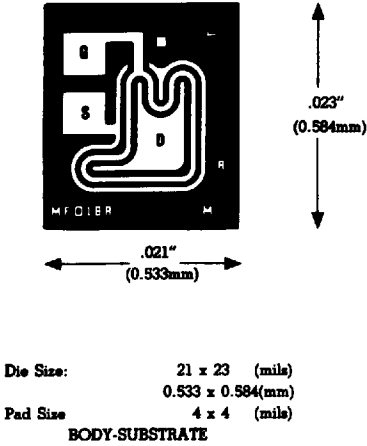


PRODUCT CATALOG

N-CHANNEL ENHANCEMENT MOS FET

CHIP NUMBER

FMN1.2



CONTACT METALLIZATION

Top Contact: > 12,000 Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

- It is advisable that:
- a) the die be eutectically mounted with gold silicon preform 98/2%.
  - b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

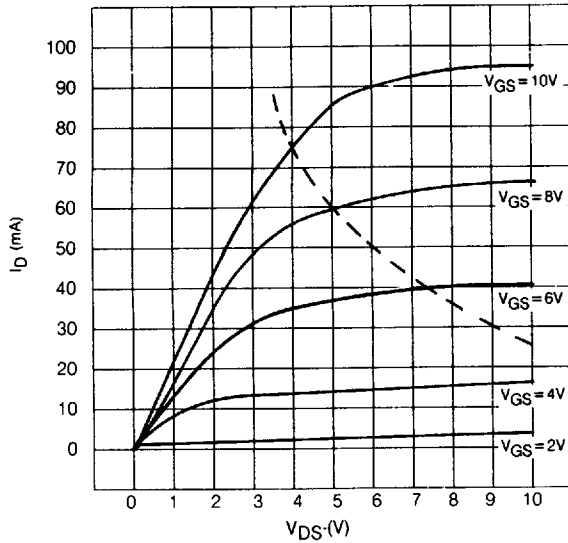
TYPICAL ELECTRICAL CHARACTERISTICS

| PARAMETER | MIN. | TYP | MAX. | UNIT | TEST CONDITIONS                          |
|-----------|------|-----|------|------|------------------------------------------|
| BVDSS     | 20   | 33  |      | V    | $I_D = 1.0\mu A, V_{GS} = 0, V_{BS} = 0$ |
| IDSS      |      | .01 | 10   | nA   | $V_{DS} = 10V, V_{GS} = 0, V_{BS} = 0$   |
| IGSS      |      | 0.2 | 5    | pA   | $V_{GB} = \pm 25V, V_{DB}, = U_{SB} = 0$ |
| VTH       | 0.1  | 1.0 | 2.5  | V    | $V_{DS} = V_{GS} = V_{TH}, I_D = 1\mu A$ |
| gfs       | 8.0  | 10  |      | ms   | $V_{DS} = 10V, I_D = 20mA, f = 1KHz$     |
| RDS       |      | 70  | 100  | Ω    | $I_{DS} = 0.1mA, V_{GS} = 5.0V$          |
| Ciss      |      |     | 4.5  | pF   | $V_{DS} = 15V, I_D = 20mA, f = 1MHz$     |
| Coss      |      |     | 1.3  | pF   | $V_{DS} = 15V, I_D = 20mA, f = 1MHz$     |
| Crss      |      |     | 1.2  | pF   | $V_{DS} = 15V, I_D = 20mA, f = 1MHz$     |

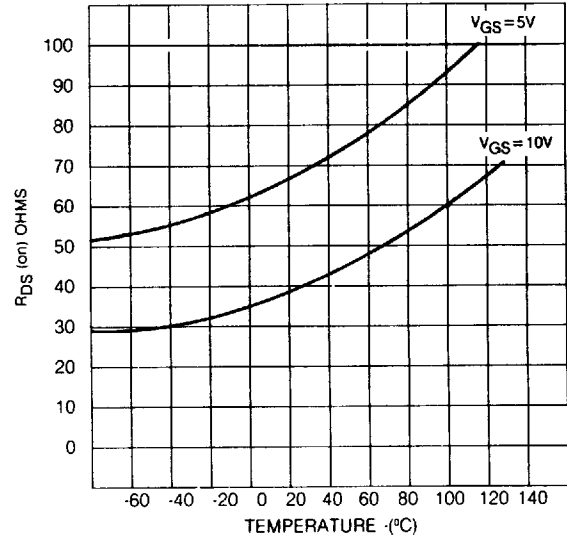
## N-CHANNEL ENHANCEMENT MOS FET

CHIP TYPE FMN1.2

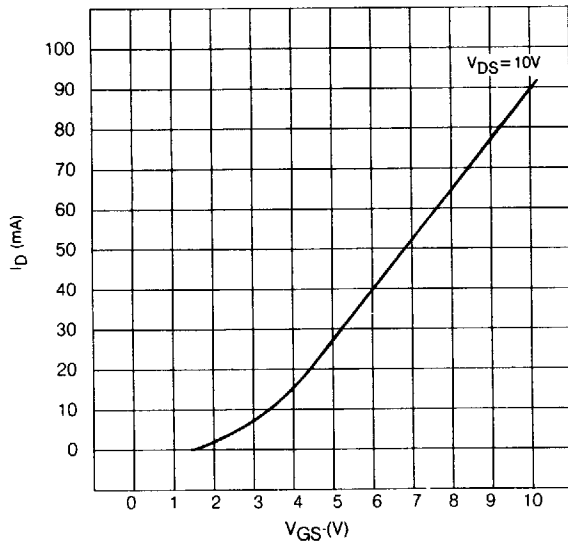
DRAIN CURRENT VS  
DRAIN-TO-SOURCE VOLTAGE



DRAIN-TO-SOURCE RESISTANCE  
VS TEMPERATURE



DRAIN CURRENT VS  
GATE-TO-SOURCE VOLTAGE



TRANSCONDUCTANCE VS  
GATE-TO-SOURCE VOLTAGE

